

# MJ15023 (PNP), MJ15025 (PNP)



## Silicon Power Transistors

The MJ15023 and MJ15025 are power transistors designed for high power audio, disk head positioners and other linear applications.

### Features

- High Safe Operating Area
- High DC Current Gain
- Complementary to MJ15022 (NPN), MJ15024 (NPN)
- These Devices are Pb-Free and are RoHS Compliant\*

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MJ15023 MJ15025	$V_{CEO}$	200 250	Vdc
Collector-Base Voltage MJ15023 MJ15025	$V_{CBO}$	350 400	Vdc
Emitter-Base Voltage	$V_{EBO}$	5	Vdc
Collector-Emitter Voltage	$V_{CEX}$	400	Vdc
Collector Current – Continuous (Note 1)	$I_C$	16	Adc
Collector Current – Peak (Note 1)	$I_{CM}$	30	Adc
Base Current – Continuous	$I_B$	5	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	250 1.43	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle  $\leq 10\%$ .

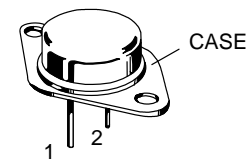
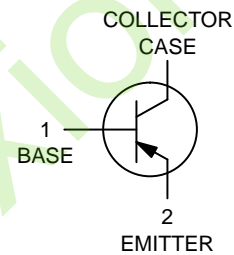
### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.70	$^\circ\text{C/W}$

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**16 AMPERES  
SILICON POWER TRANSISTORS  
200 – 250 VOLTS, 250 WATTS**



**TO-204 (TO-3)  
CASE 1-07  
STYLE 1**

### MARKING DIAGRAM



MJ1502x = Device Code  
x = 3 or 5  
G = Pb-Free Package  
A = Assembly Location  
Y = Year  
WW = Work Week  
MEX = Country of Origin

### ORDERING INFORMATION

Device	Package	Shipping
MJ15023G	TO-204 (Pb-Free)	100 Units / Tray
MJ15025G	TO-204 (Pb-Free)	100 Units / Tray

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MJ15023 (PNP), MJ15025 (PNP)

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Sustaining Voltage (Note 2) ( $I_C = 100\text{ mAdc}$ , $I_B = 0$ ) MJ15023 MJ15025	$V_{CE(sus)}$	200 250	– –	–
Collector Cutoff Current ( $V_{CE} = 200\text{ Vdc}$ , $V_{BE(off)} = 1.5\text{ Vdc}$ ) MJ15023 ( $V_{CE} = 250\text{ Vdc}$ , $V_{BE(off)} = 1.5\text{ Vdc}$ ) MJ15025	$I_{CEX}$	– –	250 250	$\mu\text{Adc}$
Collector Cutoff Current ( $V_{CE} = 150\text{ Vdc}$ , $I_B = 0$ ) MJ15023 ( $V_{CE} = 200\text{ Vdc}$ , $I_B = 0$ ) MJ15025	$I_{CEO}$	– –	500 500	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{CE} = 5\text{ Vdc}$ , $I_B = 0$ ) Both	$I_{EBO}$	–	500	$\mu\text{Adc}$
<b>SECOND BREAKDOWN</b>				
Second Breakdown Collector Current with Base Forward Biased ( $V_{CE} = 50\text{ Vdc}$ , $t = 0.5\text{ s}$ (non-repetitive)) ( $V_{CE} = 80\text{ Vdc}$ , $t = 0.5\text{ s}$ (non-repetitive))	$I_{S/b}$	5 2	– –	Adc
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = 8\text{ Adc}$ , $V_{CE} = 4\text{ Vdc}$ ) ( $I_C = 16\text{ Adc}$ , $V_{CE} = 4\text{ Vdc}$ )	$h_{FE}$	15 5	60 –	–
Collector–Emitter Saturation Voltage ( $I_C = 8\text{ Adc}$ , $I_B = 0.8\text{ Adc}$ ) ( $I_C = 16\text{ Adc}$ , $I_B = 3.2\text{ Adc}$ )	$V_{CE(sat)}$	– –	1.4 4.0	Vdc
Base–Emitter On Voltage ( $I_C = 8\text{ Adc}$ , $V_{CE} = 4\text{ Vdc}$ )	$V_{BE(on)}$	–	2.2	Vdc
<b>DYNAMIC CHARACTERISTICS</b>				
Current–Gain – Bandwidth Product ( $I_C = 1\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $f_{test} = 1\text{ MHz}$ )	$f_T$	4	–	MHz
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f_{test} = 1\text{ MHz}$ )	$C_{ob}$	–	600	pF

2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

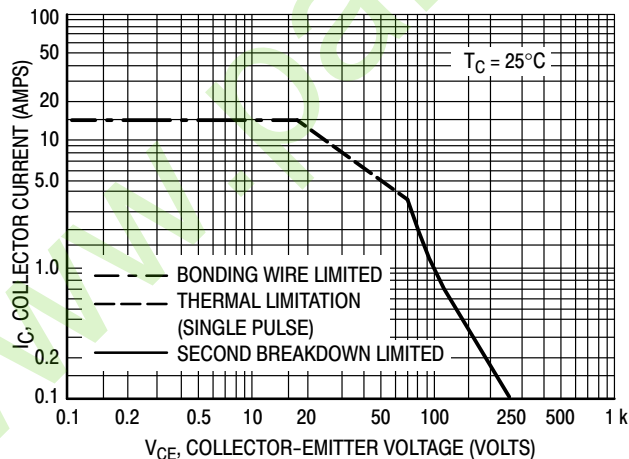


Figure 1. Active–Region Safe Operating Area

There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on  $T_{J(pk)} = 200^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

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## TYPICAL CHARACTERISTICS

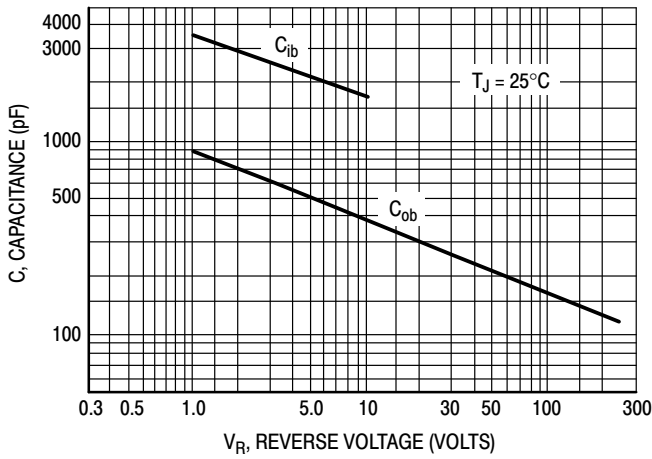


Figure 2. Capacitances

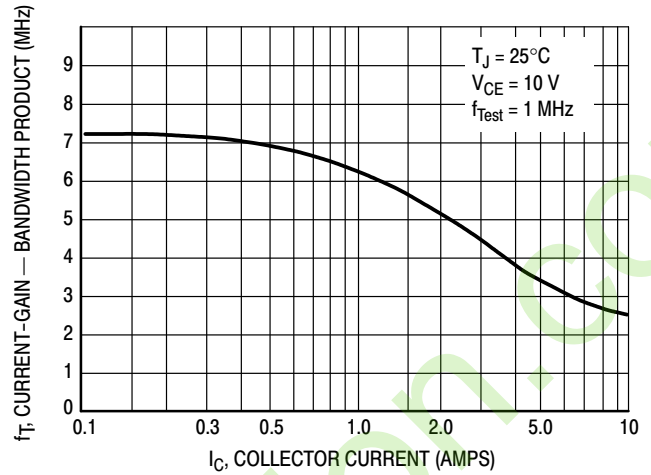


Figure 3. Current-Gain - Bandwidth Product

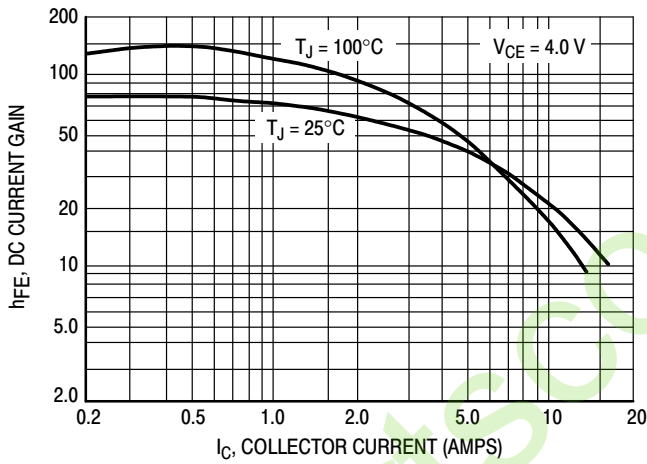


Figure 4. DC Current Gain

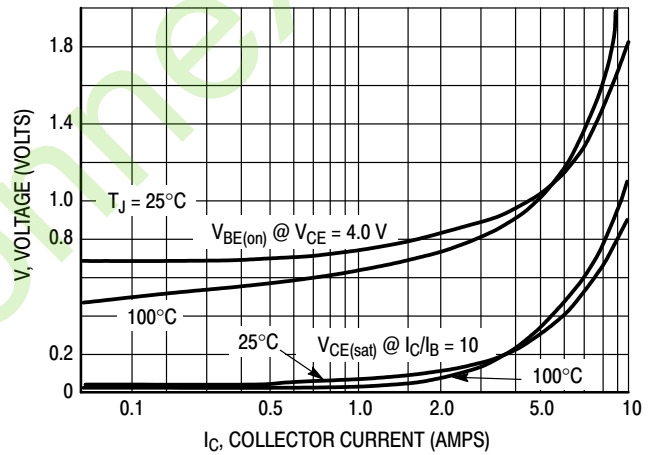


Figure 5. "On" Voltages

